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(54) **GRAPHENE BARRIER LAYER**

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(57) **ABSTRACT**

Interconnect structures and method of forming the same are disclosed herein. An exemplary interconnect structure includes a first contact feature in a first dielectric layer, a second dielectric layer over the first dielectric layer, a third dielectric layer over the second dielectric layer, a second contact feature extending through the second dielectric layer and the third dielectric layer, and a graphene layer between the second contact feature and the third dielectric layer.

